

## 60V N-Channel Power MOSFET



**TO-220** 

**ITO-220** 

Pin Definition:

1. Gate 2. Drain

3. Source

**Key Parameter Performance** 

Parameter		Value	Unit	
$V_{DS}$		60	V	
R <sub>DS(on)</sub> (max)	V <sub>GS</sub> = 10V	23		
	V <sub>GS</sub> = 4.5V	28	mΩ	
Q <sub>q</sub>		28	nC	



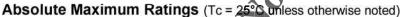


#### **Features**

- 100% avalanche tested
- Fast Switching

#### **Ordering Information**

- L	,	W Z		
1		1	$Q_g$	28
TO-252		- -		•
(DPAK)				
2				
2 3			(3)	
1			3	
		, O	Disabil	D:
<u>Features</u>			Block	<u>Diagram</u>
<ul> <li>100% avalanche teste</li> </ul>	ed			Drain
<ul> <li>Fast Switching</li> </ul>		100		9
Ordering Informatio	n		100	
Ordering informatio	<u>''</u>	0> 0		
Part No.	Package	Packing		البر
TSM230N06CZ C0G	TO-220	50pc <b>s / Tub</b> e	Tended Gate o-	<b>⊿i≒</b> ↑
TSM230N06CI C0G	JTO 220	50pcs / Tube		
TSM230N06CP ROG	TO-252	2.5kpcs / 13" Reel		
Note: "G" denotes for Halogen	- and Antimony-	free as those which contain		Y
<900ppm bromine, <900 <1000ppm antimony co		1500ppm total Br + Cl) and		Source
			N-Channe	el MOSFET



Parameter		Symbol		1124		
			TO-220	ITO-220	DPAK	Unit
Drain-Source Voltage		$V_{DS}$		V		
Gate-Source Voltage		$V_{GS}$		V		
Continuous Drain Current (Note 1)	Tc = 25°C	I <sub>D</sub>	50*			Α
	Tc = 100°C		32*			Α
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	200			Α
Single Pulse Avalanche Energy (Note 3)		E <sub>AS</sub>	42			mJ
Power Dissipation @ T <sub>C</sub> = 25°C		$P_{D}$	104	42	53	W
Operating Junction Temperature		TJ	150			°C
Storage Temperature Range		$T_{STG}$	-55 to +150			°C



## 60V N-Channel Power MOSFET



#### **Thermal Performance**

	0 1 1		1114		
Parameter	Symbol	TO-220	ITO-220	DPAK	Unit
Thermal Resistance - Junction to Case	R <sub>eJC</sub>	1.2	3	2	0000
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	62	62	62	°C/W

**Electrical Specifications** (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	60			V
Drain Course On State Decistance	$V_{GS} = 10V, I_D = 20A$			20	23	~~
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 12A$	R <sub>DS(ON)</sub>		23	28	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	1.2	1.8	2.5	V
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 60V, V <sub>eS</sub> = 0V	~0			1	
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 48V, T <sub>1</sub> = 125°C	I <sub>DSS</sub>			10	μA
Gate Body Leakage	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	) I <sub>GSS</sub>	A		±100	nA
Forward Transconductance (Note 4)	$V_{DS} = 10V, I_{D} = 10A$	g <sub>fs</sub>	2-	9		S
Dynamic	· O > O -		<b>Y</b>			
Total Gate Charge (Note 4,5)	$V_{DS} = 30V_{A}I_{R} = 15A$	Qg		28		
Gate-Source Charge (Note 4,5)		Qgs		3.5		nC
Gate-Drain Charge (Note 4,5)	V <sub>GS</sub> = 10V	$Q_{gd}$		6.5		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C <sub>iss</sub>		1680		
Output Capacitance	f > 1.0MHz	C <sub>oss</sub>		115		pF
Reverse Transfer Capacitance	57 1.0IVII 12	$C_{rss}$		85		
Switching	X					
Turn-On Delay Time (Note 4,5))	40	t <sub>d(on)</sub>		7.2		
Turn-On Rise Time (Note 4,5))	$V_{DD} = 30V, I_D = 1A,$	t <sub>r</sub>		38		ne
Turn-Off Delay Time (Note 4,5)	$V_{GS} = 10V, R_G = 6\Omega$	$t_{d(off)}$		34		ns
Turn-Off Fall Time (Note 4,5)		t <sub>f</sub>		8.2		
Source-Drain Diode Ratings and Ch	aracteristic					
Maximum Continuous Drain-Source		ı			50	Α
Diode Forward Current	Integral reverse diode	I <sub>S</sub>			30	A
Maximum Pulse Drain-Source Diode	in the MOSFET	I <sub>SM</sub>			200	Α
Forward Current		ISM			200	
Diode-Source Forward Voltage	$V_{GS} = 0V$ , $I_S = 1A$	$V_{SD}$			1	V
Reverse Recovery Time (Note 4)	$V_{GS} = 0V, I_{S} = 1A$	t <sub>rr</sub>		19.6		ns
Reverse Recovery Charge (Note4)	$dI_F/dt = 100A/\mu s$	$Q_{rr}$		14.2		nC

#### Note:

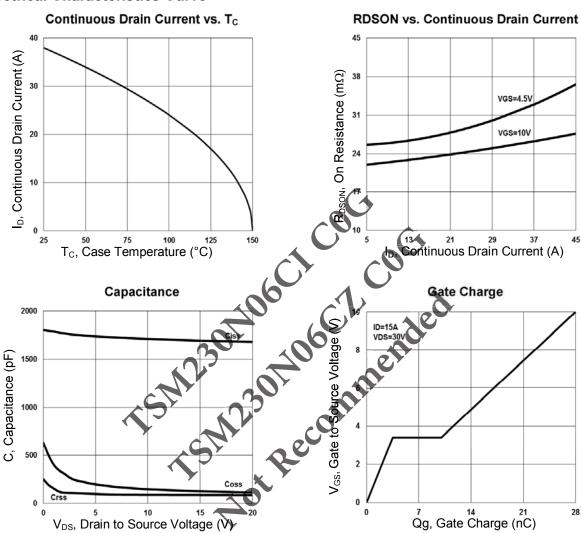
- 1. Limited by maximum junction temperature
- 2. Pulse width limited by safe operating area
- 3. L = 0.1mH,  $I_{AS}$  = 29A,  $V_{DD}$  = 25V,  $R_{G}$  = 25 $\Omega$ , Starting  $T_{J}$  = 25 $^{\circ}$ C
- 4. Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- 5. Switching time is essentially independent of operating temperature.



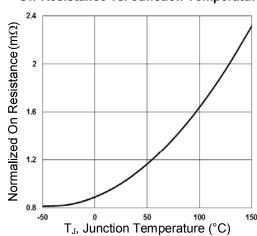
## 60V N-Channel Power MOSFET



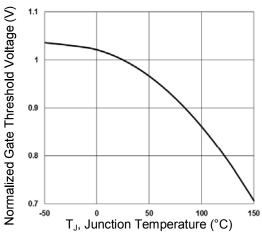
#### **Electrical Characteristics Curve**



#### On-Resistance vs. Junction Temperature



#### Threshold Voltage vs. Junction Temperature



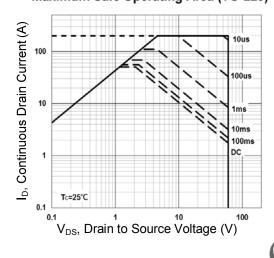


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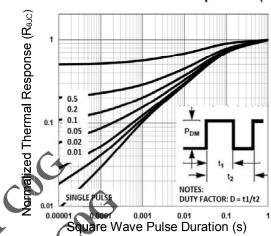


#### **Electrical Characteristics Curve**

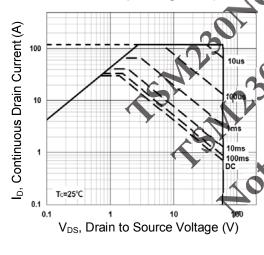
#### Maximum Safe Operating Area (TO-220)



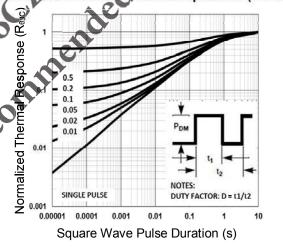
#### Normalized Thermal Transient Impedance (TO-220)



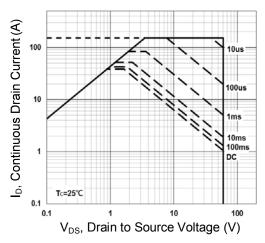
#### Maximum Safe Operating Area (ITO-220)



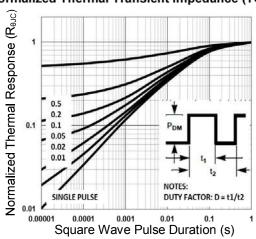
Normalized Thermal Transient Impedance (ITO-220)



#### Maximum Safe Operating Area (TO-252)



#### Normalized Thermal Transient Impedance (TO-252)



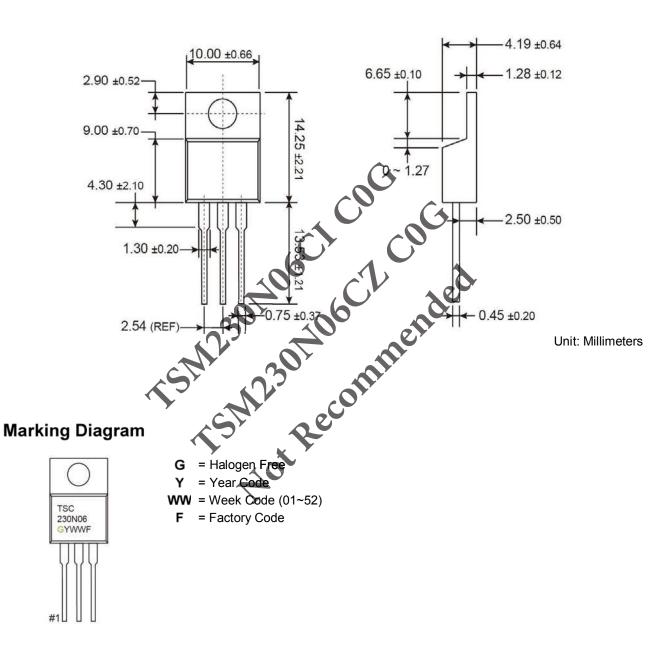






## 60V N-Channel Power MOSFET

## **TO-220 Mechanical Drawing**



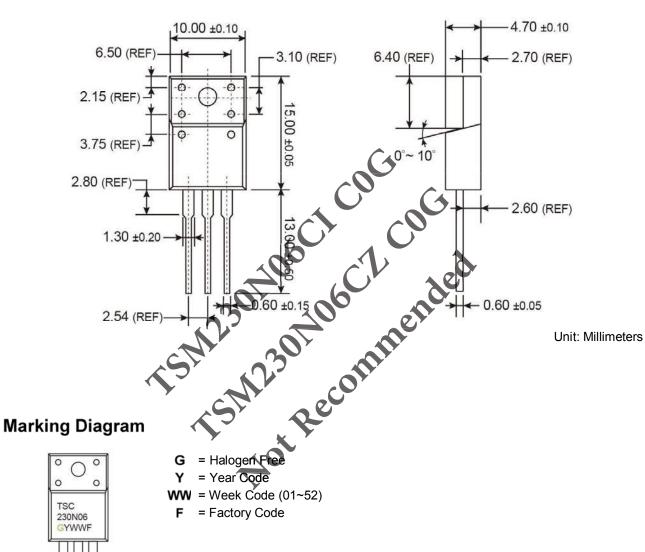






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## **ITO-220 Mechanical Drawing**



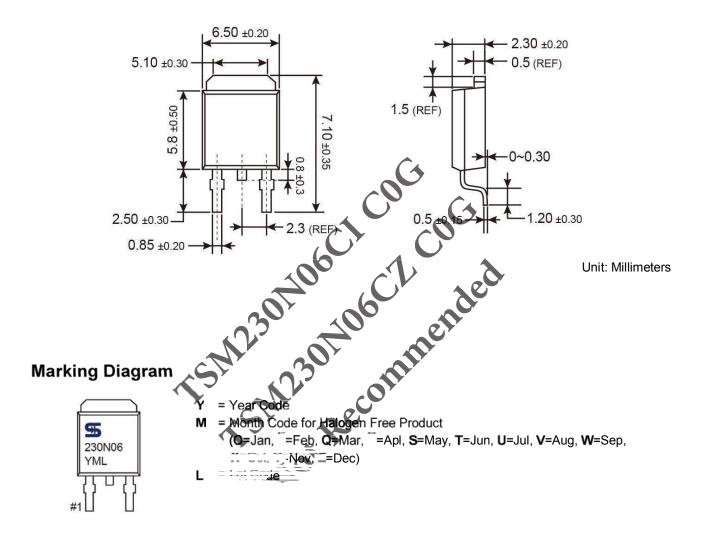
TSC 230N06 **GYWWF** 



## 60V N-Channel Power MOSFET



# **TO-252 Mechanical Drawing**





### 60V N-Channel Power MOSFET



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